EAST - [resistor.wsp:1]

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Drafts
Pending
Active
L1: (1) ("6709982").PN.
L2: (115) fin adj field adj effect or (FinFET)
L3: (59) 2 and fin.clm.
L4: (30) 3 and (transistor.clm. or transistor.ab.)
L5: (21) 4 and (trench$2 or hole$1 or opening$1)
Failed
Saved
(0) ("(thinadjfilm)nearresistor").PN.
(0) ("(thinadjfilm)nearresistor").PN.
(150130) thin adj film
(14857) (thin adj film) and resistor
(2054) ((thin adj film) and resistor) and ((thin adj film)
(1735) (((thin adj film) and resistor) and ((thin adj film)
(801) ((((thin adj film) and resistor) and ((thin adj film)
(499) (((((thin adj film) and resistor) and ((thin adj film
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(34) (((((((thin adj film) and resistor) and ((thin adj fil
(98) ((((((thin adj film) and resistor) and ((thin adj film)
(1010) (dual adj damas$5).clm.

Browse Search Clear

DBS IBMAT;IBMPROS

Default operator: OR

Words

Highlight patterns globally

5 and (trench$2 or hole$1 or opening$1)

Display Mark Search Text Image

	U	I	PT	P	Document ID	Issue Dat	Pages	Title	Current OR	Current XR	Retrieval	Inventor	S	C
1					US 20040092060	20040513	12	FIN field effect transistor with self-al	438/157	257/66; 257/E21.41		Gambino, Jeffrey P. et al.		
2					US 20040075122	20040422	17	Double and triple gate MOSFET devices and meth	257/288	257/E21.41 5;		Lin, Ming-Ren et al.		
3					US 20040038464	20040226	18	Multiple-plane FinFET CMOS	438/151	438/152; 438/168		Fried, David M. et al.		
4					US 20040036118	20040226	48	Concurrent Fin-FET and thick-body device fabri	257/347	257/E21.70 3;		Abadeer, Wagdi W. et al.		
5					US 20040031979	20040219	64	Strained-semiconductor-on-insulator device str	257/233	257/235; 257/297;		Lochtefeld, Anthony J. et al.		
6					US 20030201458	20031030	24	Strained fin fets structure and method	257/192	257/E21.41 1;		Clark, William F. et al.		
7					US 20030197194	20031023	19	FIN MEMORY CELL AND	257/200			Fried, David M. et al.		
8					US 20030178681	20030925	38	Strained fin FETs structure and method	257/347	257/E21.41 1;		Clark, William F. et al.		
9					US 20030178677	20030925	38	STRAINED FIN FETS STRUCTURE AND METHOD	257/347	257/E21.41 1;		Clark, William F. et al.		
10					US 20030178670	20030925	14	Finfet CMOS with NVRAM capability	257/315	257/E21.20 9;		Fried, David M. et al.		
11					US 20030102518	20030605	22	Finfet SRAM cell using low mobility plane for	257/401	257/350; 257/368;		Fried, David M. et al.		
12					US	20030605	18	Multiple-plane finFET	257/255			Fried, David M. et		

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